

HIGH VOLTAGE APPLICATION.
TELEPHONE APPLICATION.

FEATURES

- Complementary to MPSA42/43.

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage	MPSA92	V_{CBO}	-300	V
	MPSA93		-200	
Collector-Emitter Voltage	MPSA92	V_{CEO}	-300	V
	MPSA93		-200	
Emitter-Base Voltage		V_{EBO}	-5.0	V
Collector Current		I_C	-500	mA
Emitter Current		I_E	500	mA
Collector Power Dissipation		P_C	625	mW
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55 ~ 150	°C



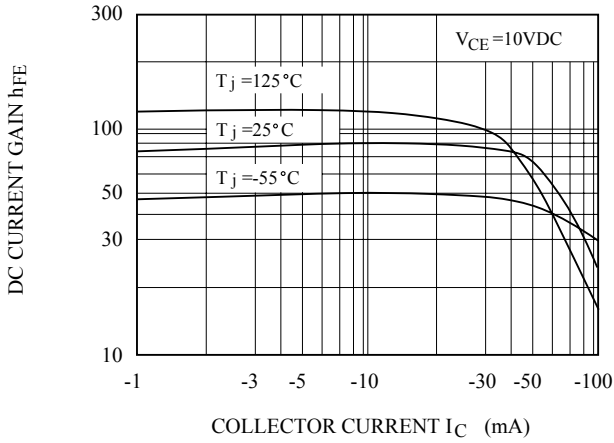
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	MPSA92	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-300	-	-	V
	MPSA93			-200	-	-	
Collector-Emitter Breakdown Voltage	MPSA92	$V_{(BR)CEO}$	$I_C = -1.0mA, I_B = 0$	-300	-	-	V
	MPSA93			-200	-	-	
Collector Cut-off Current	MPSA92	I_{CBO}	$V_{CB} = -300V, I_E = 0$	-	-	-0.25	μA
	MPSA93		$V_{CB} = -150V, I_E = 0$	-	-	-0.25	
Emitter Cut-off Current		I_{EBO}	$V_{EB} = -3V, I_C = 0$	-	-	-0.1	μA
DC Current Gain	* h_{FE}		$I_C = -1.0mA, V_{CE} = -10V$	25	-	-	
			$I_C = -10mA, V_{CE} = -10V$	40	-	-	
			$I_C = -30mA, V_{CE} = -10V$	25	-	-	
Collector-Emitter Saturation Voltage		* $V_{CE(sat)}$	$I_C = -20mA, I_B = -2.0mA$	-	-	-0.5	V
Base-Emitter Saturation Voltage		* $V_{BE(sat)}$	$I_C = -20mA, I_B = -2.0mA$	-	-	-0.9	V
Transition Frequency		f_T	$V_{CE} = -20V, I_C = -10mA, f = 100MHz$	50	-	-	MHz
Collector Output Capacitance	MPSA92	C_{ob}	$V_{CB} = -20V, I_E = 0, f = 1MHz$	-	-	6.0	pF
	MPSA93			-	-	8.0	

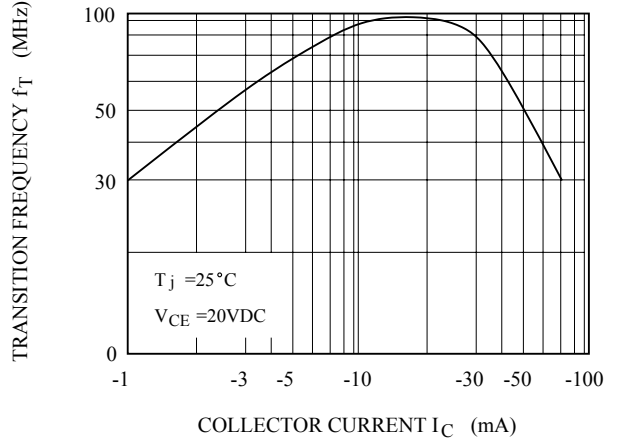
*Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

MPSA92/93

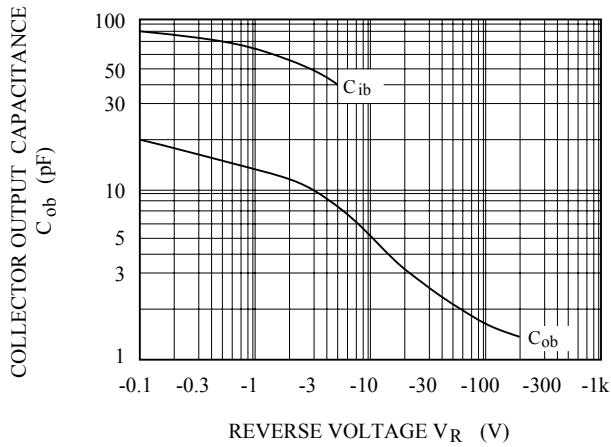
$h_{FE} - I_C$



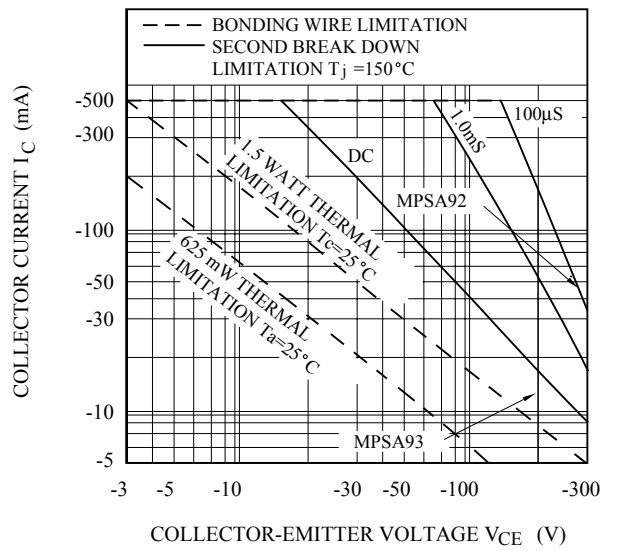
$f_T - I_C$



$C_{ob} - V_R$



$I_C - V_{CE}$



$V_{BE(sat)}, V_{CE(sat)} - I_C$

